

**AMENDMENTS TO THE CLAIMS**

1. (Original) A light device comprising:

- a GaN-based layer;
- a high concentration GaN-based layer formed on the GaN-based layer;
- a first metal-Ga compound layer formed on the high concentration GaN-based layer;
- a first metal layer formed on the first metal-Ga compound layer;
- a third metal-Al compound layer formed on the first metal layer; and
- a conductive oxidation preventive layer formed on the third metal-Al compound layer.

2. (Original) A light device comprising:

- a GaN-based layer;
- a high concentration GaN-based layer formed on the GaN-based layer;
- a transparent electrode layer formed above the high concentration GaN-based layer;
- a first metal-Ga compound layer formed on the transparent electrode layer;
- a first metal layer formed on the first metal-Ga compound layer;
- a third metal-Al compound layer formed on the first metal layer; and
- a conductive oxidation preventive layer formed on the third metal-Al compound layer.

3. (Original) A light device comprising:

- a GaN-based layer;
- a high concentration GaN-based layer formed on the GaN-based layer;
- a first metal-Ga-N compound layer formed on the high concentration GaN-based layer;

- a first metal layer formed on the first metal-Ga-N compound layer;
- a third metal-Al compound layer formed on the first metal layer; and
- a conductive oxidation preventive layer formed on the third metal-Al compound layer.

4. (Original) The light device of any one according to claims 1 to 3, wherein the GaN-based layer is P-type or N-type.

5. (Original) The light device of any one according to claims 1 to 3, wherein the first metal layer is of one selected from the group consisting of Cr, V and W.

6. (Original) The light device of any one according to claims 1 to 3, wherein the first metal layer is of a metal or compound having a high reactivity with Ga and N.

7. (Original) The light device of any one according to claims 1 to 3, wherein the third metal is of one selected from the group consisting of Ni, Pt and Pd.

8. (Original) The light device of any one according to claims 1 to 3, wherein the third metal is of a metal or compound having a high reactivity with Al.

9. (Original) The light device of any one according to claims 1 to 3, wherein the third metal is of a metal or a compound not having a reactivity with the material forming the conductive oxidation preventive layer.

10. (Original) The light device of any one according to claims 1 to 3, wherein the conductive oxidation preventive layer is of Au, or is of a multi-metal or compound of two or more kinds containing Au.

11-52. (Cancelled)

53. (Previously Presented) The light device of any one according to claims 1 to 3, wherein the light device comprises an NP-type light emitting device or an NPN-type light emitting device.

54. (New) The light device of any one according to claims 1 to 3, wherein the first metal layer is of one selected from the group consisting of Cr, V and W, and the third metal is of one selected from the group consisting of Ni, Pt and Pd.